



Drafts  
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Active

- L1: (9) ((electron near2 beam) and gun and primary and (sample or object or material or semiconductor) and separatS3 and secondary and lens and acceleratS3 and (optical near2 system) and detector and deflectS3 and scanning).clm.
- L2: (1) ((electron near2 beam) and gun and primary and (sample or object or material or semiconductor) and separatS3 and secondary and lens and acceleratS3 and (optical near2 system) and detector and deflectS3 and memorS3 and switchS3 and CPU and (image near2 processS3)).clm.
- L3: (1) ((electron near2 beam) and gun and cathode and wehnelt and electrode and anode and (multiemitter or (multi adj emitter)) and heatS3 and (adjustS4 near2 mechanism) and direction and tilt and perpendicular and plane).clm.
- L4: (0) ((electron near2 beam) and gun and primary and (sample or object or material or semiconductor) and separatS3 and secondary and lens and acceleratS3 and (optical near2 system) and guidS3 and director and demagnification and image and detector and (multiaperture or (multi adj aperture))).clm.

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1	BRS	L1	9 ((electron near2 beam) and gun and primary and (sample or object or material or semiconductor) and separatS3 and secondary and lens and acceleratS3 and (optical near2 system) and detector and deflectS3 and scanning).clm.	US-PGPUB	2006/11/22 10:24		
2	BRS	L2	1 ((electron near2 beam) and gun and primary and (sample or object or material or semiconductor) and separatS3 and secondary and lens and acceleratS3 and (optical near2 system) and detector and deflectS3 and memorS3 and switchS3 and CPU and (image near2 processS3)).clm.	US-PGPUB	2006/11/22 10:21		
3	BRS	L3	1 ((electron near2 beam) and gun and cathode and wehnelt and electrode and anode and (multiemitter or (multi adj emitter)) and heatS3 and (adjustS4 near2 mechanism) and direction and tilt and perpendicular and plane).clm.	US-PGPUB	2006/11/22 10:23		
4	BRS	L4	0 ((electron near2 beam) and gun and primary and (sample or object or material or semiconductor) and separatS3 and secondary and lens and acceleratS3 and (optical near2 system) and guidS3 and director and demagnification and image and detector and (multiaperture or (multi adj aperture))).clm.	US-PGPUB	2006/11/22 10:27		

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((electron near2 beam) and gun and primary and (sample or object or material or semiconductor) and separatiS3 and secondary and lens and acceleratiS3 and (optical near2 system) and detector and deflectS3 and scanning).clm.

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U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	<input checked="" type="checkbox"/>	US 20060243906 A1	20061102	24	Inspection method and inspection system using charged particle beam	250/307		Fukada; Atsuko et al.
2	<input checked="" type="checkbox"/>	US 20060097200 A1	20060511	29	Electron beam apparatus and a device manufacturing method by using said electron beam apparatus	250/493.1		Nakasaji; Mamoru et al.
3	<input checked="" type="checkbox"/>	US 20050263715 A1	20051201	57	Objective lens, electron beam system and method of inspecting defect	250/396ML	250/310; 250/311	Nakasaji, Mamoru et al.
4	<input checked="" type="checkbox"/>	US 20050133733 A1	20050623	29	Electron beam system and method of manufacturing devices using the system	250/492.1		Nakasaji, Mamoru et al.
5	<input checked="" type="checkbox"/>	US 20040135515 A1	20040715	22	Electron beam apparatus and device manufacturing method using same	315/5.41	315/14	Hamashima, Muneki et al.
6	<input checked="" type="checkbox"/>	US 20040119023 A1	20040624	29	Electron beam apparatus and a device manufacturing method by using said electron beam apparatus	250/396R		Nakasaji, Mamoru et al.
7	<input checked="" type="checkbox"/>	US 20030155509 A1	20030821	29	Electron beam system and method of manufacturing devices using the system	250/310		Nakasaji, Mamoru et al.
8	<input checked="" type="checkbox"/>	US 20020148961 A1	20021017	104	Electron beam apparatus and device production method using the electron beam apparatus	250/311		Nakasaji, Mamoru et al.
9	<input checked="" type="checkbox"/>	US 20020142496 A1	20021003	83	Electron beam apparatus and method of manufacturing semiconductor device using the apparatus	438/14	250/492.3	Nakasaji, Mamoru et al.

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 L6: (2675) (electron near2 beam) and deflectS3 and g  
 L7: (2645) 6 and (sample or object or semiconductor  
 L8: (21) 7 and (313/409 or 313/413 or 313/421)  
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BRS	L6	2675	(electron near2 beam) and deflectS3 and gun and lens and separatS3 and detectS3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/11/22 10:30		
BRS	L7	2645	6 and (sample or object or semiconductor or wafer or material)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/11/22 10:31		
BRS	L8	21	7 and (313/409 or 313/413 or 313/421)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/11/22 10:32		

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